

QUAD EXCLUSIVE OR GATE

- HIGH SPEED
- $t_{PD} = 10 \text{ ns} (TYP.) \text{ AT V}_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 1 \mu A (MAX.) AT T_A = 25 ^{\circ}C$
- HIGH NOISE IMMUNITY

 VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE ||I_{OH}| = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS

 tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS386

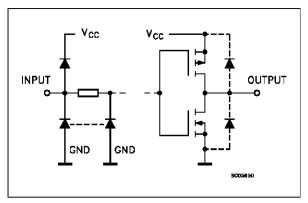
DESCRIPTION

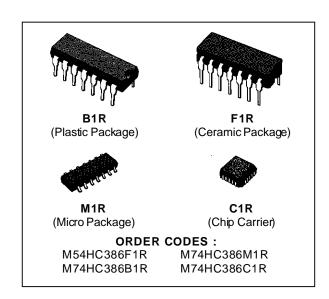
The M54/74HC386 is a high speed CMOS QUAD EXCLUSIVE-OR GATE fabricated in silicon gate C²MOS technology.

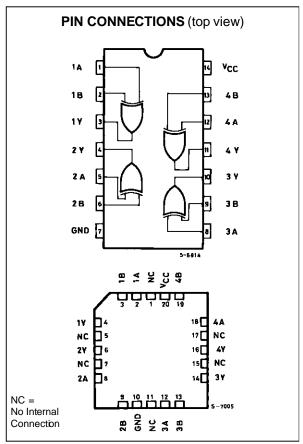
It has the same high speed performance of LSTTL combined with true CMOS low power consumption. An output buffer provides high noise immunity and a stable output.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT







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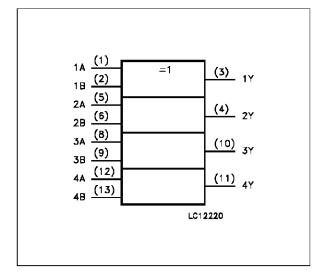
TRUTH TABLE

Α	В	Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

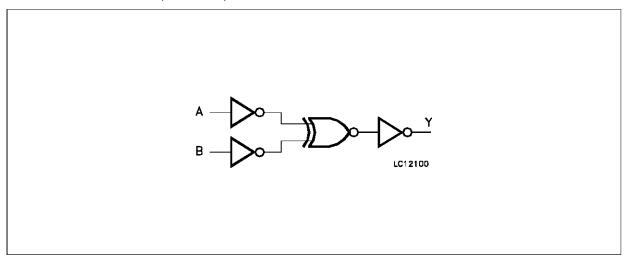
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 5, 6,	1A, 1B, 2A,	Data Inputs
8, 9, 12, 13	2B, 3A, 3B,	
	4A, 4B	
3, 4, 10, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	Vcc	Positive Supply Voltage

IEC LOGIC SYMBOL



SCHEMATIC CIRCUIT (Per Gate)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
Ιο	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≡ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
Vcc	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	သိ ဂ
t _r , t _f	Input Rise and Fall Time	$V_{CC} = 2 V$	0 to 1000	ns
		$V_{CC} = 4.5 \text{ V}$	0 to 500	
		V _{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

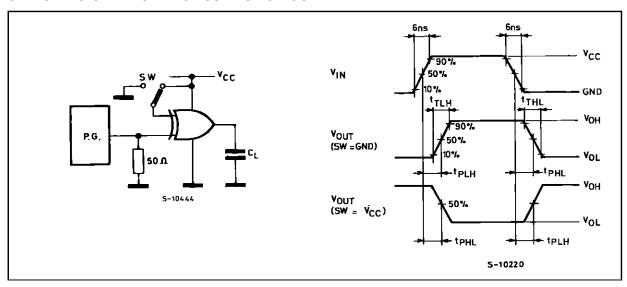
		Te	est Co	nditions				Value				
Symbol	Parameter	V _{CC} (V)			T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		()			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
VoH	High Level	2.0	V _I =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VI – VIH	I _O =-20 μA	4.4	4.5		4.4		4.4] ,,
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	VIL	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	Vı =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VI =	I _O = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	V _{IL}	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
I	Input Leakage Current	6.0	V _I = '	V _{CC} or GND			±0.1		±1		±1	μΑ
Icc	Quiescent Supply Current	6.0	V _I = '	Vcc or GND			1		10		20	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

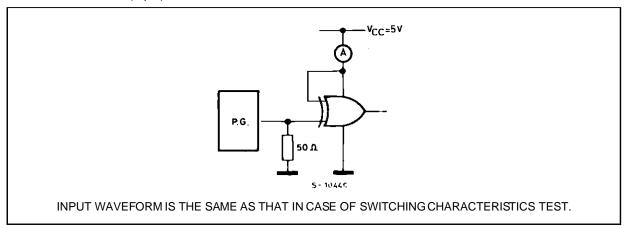
		Test Condition	ns	Value						
Symbol Parameter	Vcc		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH}	Output Transition	2.0		30	75		95		110	
t_{THL}	Time	4.5		8	15		19		22	ns
		6.0		7	13		16		19	
t _{PLH}	Propagation	2.0		48	100		125		145	
t_{PHL}	Delay Time	4.5		12	20		25		29	ns
		6.0		10	17		21		25	
C _{IN}	Input Capacitance			5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance			31						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/4$ (per Gate)

SWITCHING CHARACTERISTICS TEST CIRCUIT

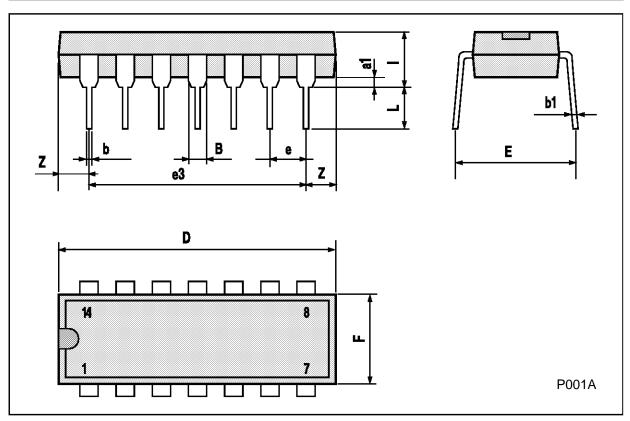


TEST CIRCUIT Icc (Opr.)



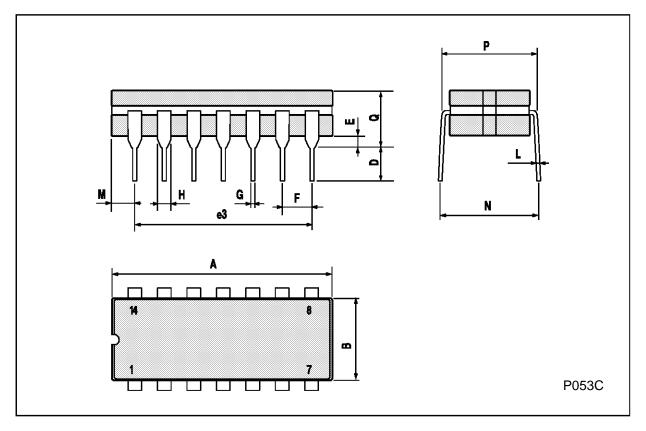
Plastic DIP14 MECHANICAL DATA

DIM.		mm		inch			
Diffi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	1.39		1.65	0.055		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		15.24			0.600		
F			7.1			0.280	
I			5.1			0.201	
L		3.3			0.130		
Z	1.27		2.54	0.050		0.100	



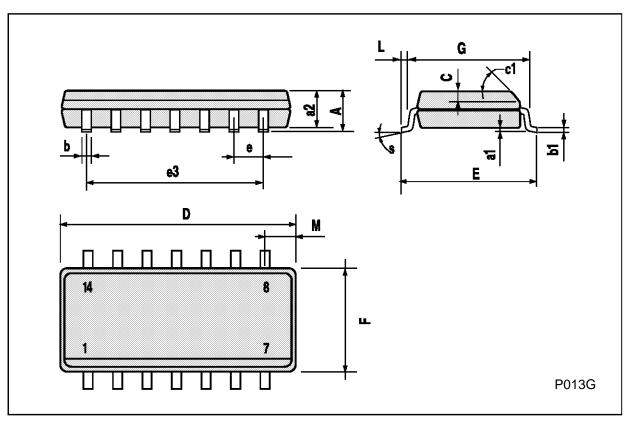
Ceramic DIP14/1 MECHANICAL DATA

DIM.		mm		inch			
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			20			0.787	
В			7.0			0.276	
D		3.3			0.130		
E	0.38			0.015			
e3		15.24			0.600		
F	2.29		2.79	0.090		0.110	
G	0.4		0.55	0.016		0.022	
Н	1.17		1.52	0.046		0.060	
L	0.22		0.31	0.009		0.012	
M	1.52		2.54	0.060		0.100	
N			10.3			0.406	
Р	7.8		8.05	0.307		0.317	
Q			5.08			0.200	



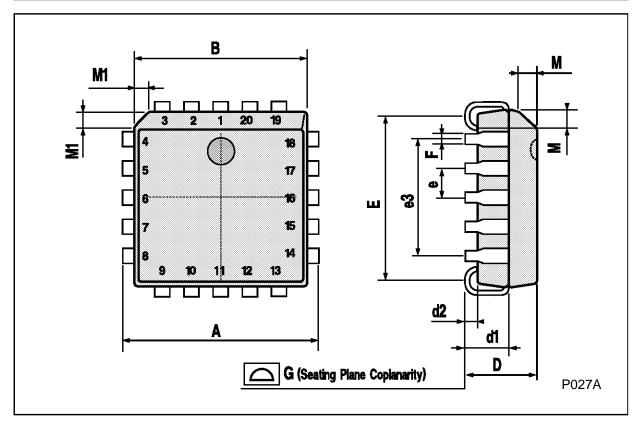
SO14 MECHANICAL DATA

DIM.		mm		inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45°	(typ.)			
D	8.55		8.75	0.336		0.344	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		7.62			0.300		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.68			0.026	
S			8° (r	nax.)			



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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